

Atty. Dkt. AMAT/3577/PDD/KPU1/WWW
108,1844
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jc490 U.S.5/10
09/336525
06/18/99

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Judy Huang

Serial No.: Unknown

Filed: Herewith

For: Plasma Treatment To Enhance Adhesion And To Minimize Oxidation Of Carbon-Containing Layers

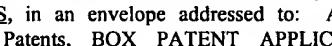
Assistant Commissioner for Patents
Washington, D.C. 20231

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Dear Sir:

Group Art Unit: Unknown

Examiner: Unknown

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CERTIFICATE OF MAILING 37 C.F.R. 1.10	
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The applicant, and the attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 C.F.R. 1.56.

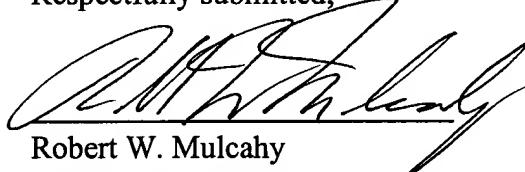
While the information submitted in this Information Disclosure Statement may be “material” pursuant to 37 C.F.R. 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is “prior art” for this invention unless specifically designated as such.

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The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

In the event a fee is required in connection with the enclosed Information Disclosure Statement, the Commissioner of Patents and Trademarks is authorized to charge Deposit Account No. 01-1651/AMAT/3577/PDD/KPU1/JW for the necessary amount.

Respectfully submitted,



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U.S. Department of Commerce, Patent and Trademark Office				Docket No.		Serial No. PRO 09/336925		
				AMAT/3577/PDD/KPU1/JW		Unknown		
LIST OF REFERENCES CITED BY APPLICANT				Applicant				
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				Filing Date		Group		
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U.S. Patent Documents								
*Examiner Initial		Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate	
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	AO	Takashi Ito, Takao Nozaki, and Hajime Ishikawa, "Direct Thermal Nitridation of Silicon Dioxide Films in Anhydrous Ammonia Gas," Optical Properties, Vol. 127, No. 9, September, 1980, Pages 2053-2057						
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U.S. Department of Commerce, Patent and Trademark Office	Docket No.	Serial No.
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LIST OF REFERENCES CITED BY APPLICANT	Applicant	
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	BI						

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	BL							

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BN	S. Takeishi, H. Kudoh, R. Shinohara, A. Tsukune, Y. Sotoc, H. Miyazawa, H. Harada, and M. Yamada, "Stabilizing Dielectric Constants of Fluorine-Doped SiO ₂ Films by N ₂ O-Plasma Annealing," J. Elelctrochem. Soc., Vol. 143, No. 1, January, 1996 © The Electrochemical Society, Inc., Pages 381-385
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